

Notice of References Cited

Application/Control No.

09/405,945

Applicant(s)/Patent Under
Reexamination
JIN ET AL

Examiner

Lynette T Umez-Eronini

Art Unit

1765

Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5907771	05-1999	Ploessi et al.	438/243
	B	US-5661064	08-1997	Figura et al.	438/396
	C	US-5376562	12-1994	Fitch et al.	438/155
	D	US-			
	F	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP-10-223897	08-1998	Japan	Atsushi	H01L 29/78
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Atsushi. Semiconductor Device and Its Manufacture, August 21, 1998, Japan Patent Office, (English translation of Abstract and Claims of JP 10223897), 3 pages.
	V	NIPPON STEEL CORP, Wiring pattern formation method for DRAM - involves forming two holes and groove on wiring layer which is patterned for electric conduction, August 21, 1998, Derwent Information LTD., (English Abstract of JP 10223897), 2 pages
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a))
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.